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CLEANING GAS

CENTRAL GLASS CO LTD

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Application No. 2000384111 , Filed 20001218 , Published 20020628

Abstract:

PROBLEM TO BE SOLVED: To provide a cleaning gas for eliminating unwanted deposits deposited on the inner wall of a thin film formation equipment or the like and in jigs, components, pipings, or the like of the equipment.

SOLUTION: The cleaning gas consists of a COF₂ gas mixed with a CF₂(OF)₂, CF₃OF, CF₃OOCF₃, or F₂ gas.

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Application No. 10206708 , Filed 19980722 , Published 20000208

Abstract:

PROBLEM TO BE SOLVED: To rapidly clean with high cleanliness and without problem of causing global warming by using a gas containing CF₃OOCF₃ in order to remove unnecessary deposits accumulated in a device for forming thin films.

SOLUTION: The unnecessary deposits accumulated in the apparatus for forming thin films are removed by using a cleaning gas containing a gas comprising CF₃OOCF₃ or CF₃OOCF₃ and a gaseous halogen or a gaseous halogenated compound. The cleaning gas can be used for cleaning reaction chamber walls, pipings and a substrate- transporting room of the apparatus for depositing B, P, W, Si, Ti, V, Nb, Ta, Se, Te, Mo, Re, Os, Ir, Sb, Ge, Au, Ag, As, Cr and compounds thereof, concretely, oxides, nitrides and carbides,

and alloys thereof. This cleaning gas exhibits high etching rate in terms of supplied molecular weight and can be easily decomposed by using a dry-type device for removing toxicity with warmed Si as a reagent for removing toxicity.

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